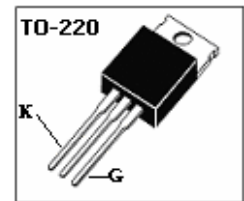
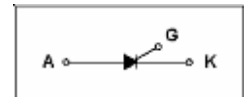


Silicon Controlled Rectifier

Features

- * Repetitive Peak Off-State Voltage : 600V
- * R.M.S On-State Current($I_{T(RMS)}$)=16A
- * Low On-State Voltage (1.35V(Typ.)@ I_{TM})
- * Non-isolated Type

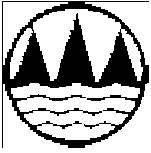


General Description

Standard gate triggering SCR is suitable for the application where requiring high bi-directional blocking voltage capability and also suitable for over voltage protection, motor control circuit in power tool, inrush current limit circuit and heating control system.

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise specified)

T_{stg}	— Storage Temperature	-----	-40~125°C
T_j	— Operating Junction Temperature	-----	-40~125°C
V_{DRM}	— Repetitive Peak Off-State Voltage	-----	600V
I_T (RMS)	— R.M.S On-State Current (180° Conduction Angles)	-----	16A
$I_{T(AV)}$	— Average On-State Current (Half Sine Wave : $T_C = 102^\circ\text{C}$)	-----	10A
I_{TSM}	— Surge On-State Current (1/2 Cycle, 60Hz, Sine Wave, Non-repetitive)	-----	200A
I^2t	— Circuit Fusing Considerations($t = 10\text{ms}$)	-----	180 A ² s
P_{GM}	— Forward Peak Gate Power Dissipation ($T_a=25^\circ\text{C}$)	-----	20W
$P_{G(AV)}$	— Forward Average Gate Power Dissipation ($T_a=25^\circ\text{C}$, $t=8.3\text{ms}$)	-----	1W
I_{FGM}	— Forward Peak Gate Current	-----	4A
V_{RGM}	— Reverse Peak Gate Voltage	-----	5V



Electrical Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Items	Min.	Typ.	Max.	Unit	Conditions
I_{DRM}	Repetitive Peak Off-State Current			10 200	μA	$V_{\text{AK}}=V_{\text{DRM}}$ $T_a=25^{\circ}\text{C}$ $T_a=125^{\circ}\text{C}$
V_{TM}	Peak On-State Voltage (1)			1.6	V	$I_{\text{TM}}=24\text{A}$, $t_p=380\mu\text{s}$
I_{GT}	Gate Trigger Current (2)			15	mA	$V_{\text{AK}}=6\text{V(DC)}$, $R_L=10\text{ ohm}$
V_{GT}	Gate Trigger Voltage (2)			1.5	V	$V_{\text{AK}}=6\text{V(DC)}$, $R_L=10\text{ ohm}$ $T_a=25^{\circ}\text{C}$
V_{GD}	Non-Trigger Gate Voltage	0.2			V	$V_{\text{AK}}=12\text{V}$, $R_L=100\text{ ohm}$ $T_a=125^{\circ}\text{C}$
I_{H}	Holding Current			20	mA	$I_T=100\text{mA}$, Gate open, $T_a=25^{\circ}\text{C}$
$R_{\text{th(j-c)}}$	Thermal Resistance			1.1	$^{\circ}\text{C/W}$	Junction to Case
$R_{\text{th(j-a)}}$	Thermal Resistance			60	$^{\circ}\text{C/W}$	Junction to Ambient
dv/dt	Critical Rate of Rise Off-state Voltage	200			$\text{V}/\mu\text{s}$	Linear slope up to $V_D=V_{\text{DRM}}67\%$ Gate open $T_j=125^{\circ}\text{C}$

1. Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.
2. R_{GK} current is not included in measurement

Performance Curves

FIGURE 1 – Gate Characteristics

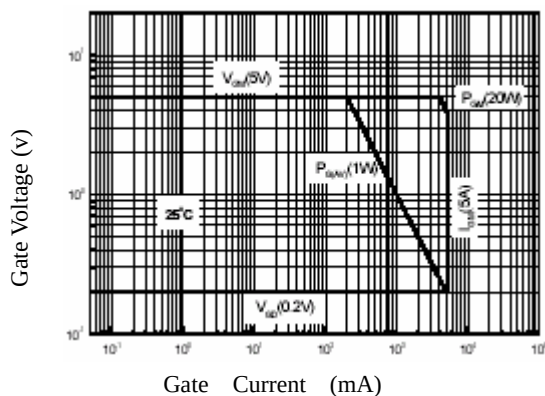
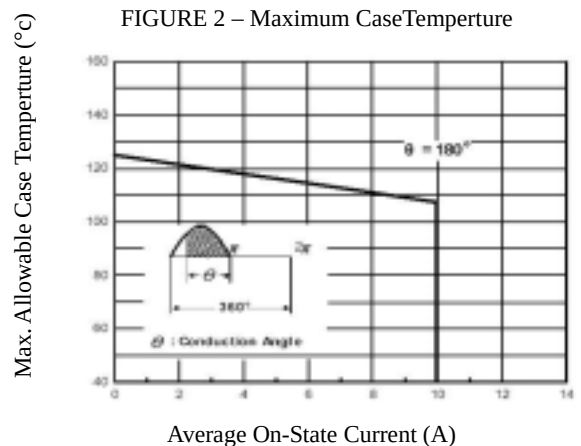


FIGURE 2 – Maximum Case Temperature



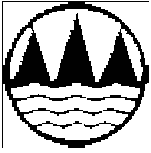


FIGURE 3-Typical Forward Voltage(V)

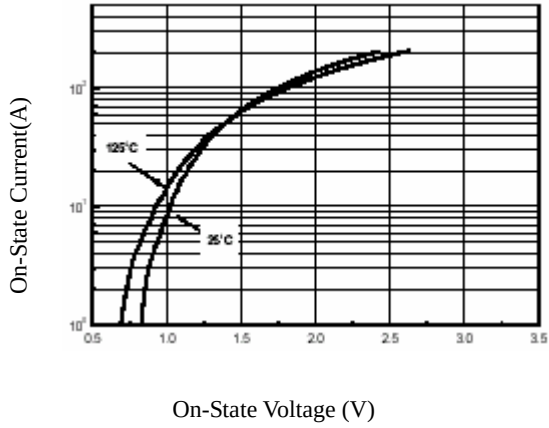


FIGURE 4-Thermal Response

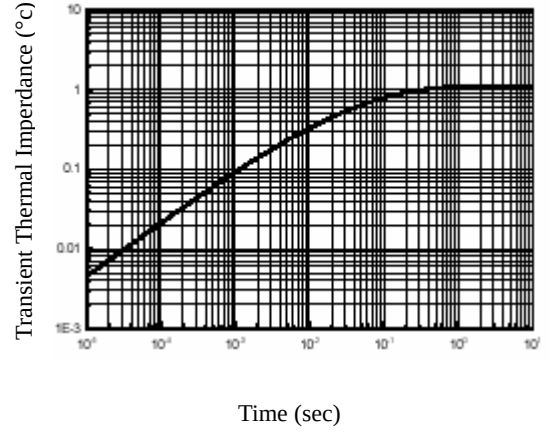


FIGURE 5-Typical Gate Trigger Voltage VS Junction Temperature

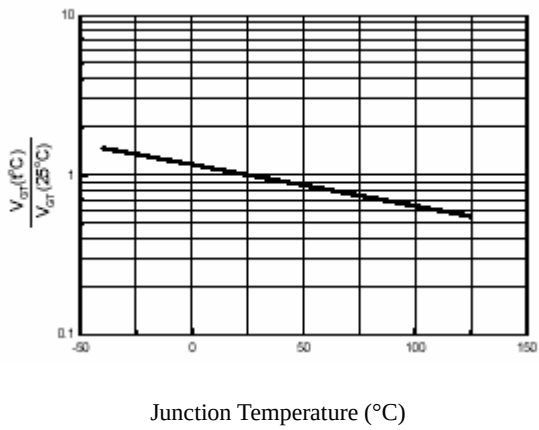


FIGURE 6-Typical Gate Trigger Current VS Junction Temperature

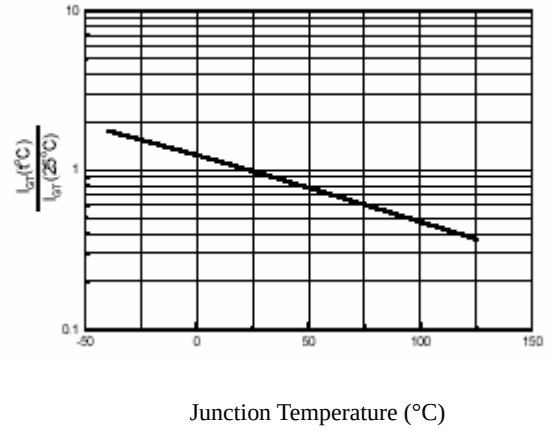


FIGURE 7-Typical Holding Current

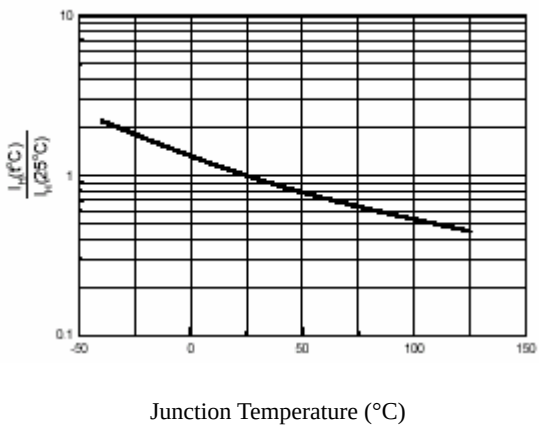


FIGURE 8-Power Dissipation

